

SILICON RECTIFIER DICE (continued)

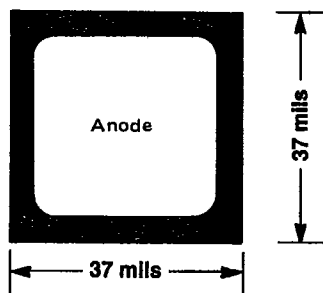
DIE NO. **IC5819**
LINE SOURCE — DRL754



This die provides performance equal to or better than that of the following device types:

1N5817
1N5818
1N5819

Designed for Schottky
Barrier low-voltage
high-frequency rectifier
applications.



Backside: Cathode

METALLIZATION —

Top* Cr Ni Au
Back Cr Ni Au

DIE THICKNESS 7 ± 2

BONDING PAD SIZE:

Anode 30 x 30 mils

*BONDING — Rectifier chips are designed for solder connections on both sides. Conductive epoxy could be substituted. The metallization is wire bondable using thermocompression or ultrasonic techniques, but adjustments in the machine settings may be necessary because of the metallization system.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$; Note 1)

Parameter	Test Conditions	Min	Max	Unit
V_{RRM}/V_R		40	—	Volts
V_F	$I_F = 1.0$ Amp	—	0.60	Volts
I_R	$V_R = 40$ Volts	—	1.0	mAdc

NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
2. Detailed device characteristics are available from your Motorola sales representative.